Colin Humphreys

List of Publications by Year
in descending order

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317 papers	8,709 citations	38742 50 h-index	62596 80 g-index
321 all docs	321 docs citations	321 times ranked	6660 citing authors

#	Article	IF	Citations
1	Solid-State Lighting. MRS Bulletin, 2008, 33, 459-470.	3.5	303
2	Machine Learning Predicts Laboratory Earthquakes. Geophysical Research Letters, 2017, 44, 9276-9282.	4.0	272
3	Prospects of III-nitride optoelectronics grown on Si. Reports on Progress in Physics, 2013, 76, 106501.	20.1	249
4	Electron-beam-induced strain within InGaN quantum wells: False indium â€œclusterâ€•detection in the transmission electron microscope. Applied Physics Letters, 2003, 83, 5419-5421.	3.3	248
5	Atom probe tomography today. Materials Today, 2007, 10, 36-42.	14.2	216
6	Optical and microstructural studies of InGaNâˆ•GaN single-quantum-well structures. Journal of Applied Physics, 2005, 97, 103508.	2.5	200
7	Carrier localization mechanisms in In<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:m	3.2	165
8	Three-dimensional atom probe studies of an InxGa1â^’xNâˆ•GaN multiple quantum well structure: Assessment of possible indium clustering. Applied Physics Letters, 2007, 90, 061903.	3.3	160
9	Dopant profiling with the scanning electron microscopeâ€”A study of Si. Journal of Applied Physics, 2002, 91, 9116-9122.	2.5	133
10	Understanding x-ray diffraction of nonpolar gallium nitride films. Journal of Applied Physics, 2009, 105, .	2.5	128
11	Chemical mapping and formation of V-defects in InGaN multiple quantum wells. Applied Physics Letters, 2000, 77, 1274-1276.	3.3	126
12	Tunable optoelectronic and ferroelectric properties in Sc-based III-nitrides. Journal of Applied Physics, 2013, 114, .	2.5	124
13	Determination of the indium content and layer thicknesses in InGaN/GaN quantum wells by x-ray scattering. Journal of Applied Physics, 2003, 94, 1565-1574.	2.5	113
14	Threading dislocation reduction in (0001) GaN thin films using SiNx interlayers. Journal of Crystal Growth, 2007, 300, 70-74.	1.5	111
15	Highlighting threading dislocations in MOVPE-grown GaN using an in situ treatment with SiH4 and NH3. Journal of Crystal Growth, 2006, 289, 506-514.	1.5	110
16	On the origin of threading dislocations in GaN films. Journal of Applied Physics, 2009, 106, .	2.5	108
17	Carrier leakage in InGaN quantum well light-emitting diodes emitting at 480 nm. Applied Physics Letters, 2003, 82, 2755-2757.	3.3	107
18	The consequences of high injected carrier densities on carrier localization and efficiency droop in InGaN/GaN quantum well structures. Journal of Applied Physics, 2012, 111, .	2.5	105

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19	Improvements in a-plane GaN crystal quality by a two-step growth process. Applied Physics Letters, 2008, 92, .	3.3	98
20	Equilibrium critical thickness for misfit dislocations in III-nitrides. Journal of Applied Physics, 2008, 104, .	2.5	94
21	Elastic constants and critical thicknesses of ScGaN and ScAlN. Journal of Applied Physics, 2013, 114, .	2.5	93
22	Characteristics and applications of micro-pixelated GaN-based light emitting diodes on Si substrates. Journal of Applied Physics, 2014, 115, .	2.5	92
23	Nanometer scale electron beam lithography in inorganic materials. Applied Physics Letters, 1984, 45, 1289-1291.	3.3	91
24	Does In form In-rich clusters in InGaN quantum wells?. Philosophical Magazine, 2007, 87, 1971-1982.	1.6	85
25	Accurate experimental determination of the Poissonâ€™s ratio of GaN using high-resolution x-ray diffraction. Journal of Applied Physics, 2007, 102, .	2.5	84
26	Electrophoretic manipulation of single DNA molecules in nanofabricated capillariesElectronic supplementary information (ESI) available: Four videoclips showing the movement of DNA molecules in nanocapillaries. See http://www.rsc.org/suppdata/lc/b3/b312592k/. Lab on A Chip, 2004, 4, 225.	6.0	82
27	Three-dimensional atom probe analysis of green- and blue-emitting InxGa1âˆ’xNâˆ•GaN multiple quantum well structures. Journal of Applied Physics, 2008, 104, .	2.5	82
28	Growth and characterisation of GaN with reduced dislocation density. Superlattices and Microstructures, 2004, 36, 393-401.	3.1	80
29	Microstructural origins of localization in InGaN quantum wells. Journal Physics D: Applied Physics, 2010, 43, 354003.	2.8	78
30	Morphological, structural, and emission characterization of trench defects in InGaN/GaN quantum well structures. Applied Physics Letters, 2012, 101, .	3.3	78
31	Electron beam writing on a 20â€Ã… scale in metal Î²â€aluminas. Applied Physics Letters, 1983, 42, 392-394.	3.3	76
32	Role of gross well-width fluctuations in bright, green-emitting single InGaNâˆ•GaN quantum well structures. Applied Physics Letters, 2007, 90, 121911.	3.3	73
33	Dislocation reduction in gallium nitride films using scandium nitride interlayers. Applied Physics Letters, 2007, 91, .	3.3	72
34	Effect of growth interruptions on the light emission and indium clustering of InGaN/GaN multiple quantum wells. Applied Physics Letters, 2001, 79, 2594-2596.	3.3	68
35	The nature of carrier localisation in polar and nonpolar InGaN/GaN quantum wells. Journal of Applied Physics, 2016, 119, .	2.5	66
36	Electronic structure of GaN andInxGa1âˆ’xNmeasured with electron energy-loss spectroscopy. Physical Review B, 2002, 66, .	3.2	63

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37	Novel fabrication method for nanometerâ€scale silicon dots and wires. Applied Physics Letters, 1993, 62, 1949-1951.	3.3	62
38	Structure and chemistry of the Si(111)/AlN interface. Applied Physics Letters, 2012, 100, .	3.3	61
39	The effects of Si doping on dislocation movement and tensile stress in GaN films. Journal of Applied Physics, 2011, 109, .	2.5	59
40	Effects of quantum well growth temperature on the recombination efficiency of InGaN/GaN multiple quantum wells that emit in the green and blue spectral regions. Applied Physics Letters, 2015, 107, .	3.3	58
41	Nanoscale-accuracy transfer printing of ultra-thin AlInGaN light-emitting diodes onto mechanically flexible substrates. Applied Physics Letters, 2013, 103, .	3.3	57
42	Structural, electronic, and optical properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>m</mml:mi></mml:math>-plane InGaN/GaN quantum wells: Insights from experiment and atomistic theory. Physical Review B, 2015, 92, .	3.2	57
43	Defect reduction in (112Â¯2) semipolar GaN grown on m-plane sapphire using ScN interlayers. Applied Physics Letters, 2009, 94, .	3.3	54
44	The impact of trench defects in InGaN/GaN light emitting diodes and implications for the â€œgreen gapâ€• problem. Applied Physics Letters, 2014, 105, .	3.3	54
45	Segregation of In to Dislocations in InGaN. Nano Letters, 2015, 15, 923-930.	9.1	54
46	Currentâ€“voltage instabilities in GaN/AlGaN resonant tunnelling structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2389-2392.	0.8	52
47	Scanning transmission electron microscopy investigation of the Si(111)/AlN interface grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, .	3.3	52
48	Mg Doping Affects Dislocation Core Structures in GaN. Physical Review Letters, 2013, 111, 025502.	7.8	52
49	High resolution quantitative two-dimensional dopant mapping using energy-filtered secondary electron imaging. Journal of Applied Physics, 2006, 100, 054901.	2.5	51
50	Carrier distribution in InGaN/GaN tricolor multiple quantum well light emitting diodes. Applied Physics Letters, 2009, 95, .	3.3	51
51	Electron-beam-induced damage in amorphous SiO₂and the direct fabrication of silicon nanostructures. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 78, 491-506.	0.6	50
52	The impact of gross well width fluctuations on the efficiency of GaN-based light emitting diodes. Applied Physics Letters, 2013, 103, .	3.3	50
53	Nanometre hole formation in MgO using electron beams. Philosophical Magazine Letters, 1990, 61, 181-193.	1.2	49
54	Misfit dislocations in In-rich InGaN/GaN quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1729-1732.	1.8	48

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55	Microstructural evolution of nonpolar (11-20) GaN grown on (1-102) sapphire using a 3D-2D method. Journal of Applied Physics, 2009, 105, .	2.5	47
56	Atom probe tomography assessment of the impact of electron beam exposure on InxGa1â^'xN/GaN quantum wells. Applied Physics Letters, 2011, 99, .	3.3	47
57	A quantitative model for doping contrast in the scanning electron microscope using calculated potential distributions and Monte Carlo simulations. Journal of Applied Physics, 2011, 109, .	2.5	47
58	High-quality III-nitride films on conductive, transparent (2Ì…01)-oriented Î²-Ga2O3 using a GaN buffer layer. Scientific Reports, 2016, 6, 29747.	3.3	46
59	Efficiency measurement of GaN-based quantum well and light-emitting diode structures grown on silicon substrates. Journal of Applied Physics, 2011, 109, .	2.5	45
60	The impact of electron beam damage on the detection of indium-rich localisation centres in InGaN quantum wells using transmission electron microscopy. Journal of Materials Science, 2006, 41, 2729-2737.	3.7	44
61	The Spatial Distribution of Threading Dislocations in Gallium Nitride Films. Advanced Materials, 2009, 21, 3941-3944.	21.0	44
62	Carrier localization in the vicinity of dislocations in InGaN. Journal of Applied Physics, 2017, 121, .	2.5	44
63	Dislocation movement in GaN films. Applied Physics Letters, 2010, 97, .	3.3	43
64	Optimisation of GaN LEDs and the reduction of efficiency droop using active machine learning. Scientific Reports, 2016, 6, 24862.	3.3	43
65	Revealing all types of threading dislocations in GaN with improved contrast in a single plan view image. Applied Physics Letters, 2004, 85, 3411-3413.	3.3	41
66	GaN-based LEDs grown on 6-inch diameter Si (111) substrates by MOVPE. Proceedings of SPIE, 2009, , .	0.8	41
67	X-ray diffraction analysis of cubic zincblende III-nitrides. Journal Physics D: Applied Physics, 2017, 50, 433002.	2.8	41
68	Xâ€•ray topography of the coherency breakdown in GexSi1â^'x/Si(100). Applied Physics Letters, 1988, 53, 2083-2085.	3.3	40
69	Structure and strain relaxation effects of defects in InxGa1â^'xN epilayers. Journal of Applied Physics, 2014, 116, .	2.5	38
70	Comment on â€œAlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxyâ€•[Appl. Phys. Lett. 81, 1729 (2002)]. Applied Physics Letters, 2003, 83, 3626-3627.	3.3	37
71	Mechanical properties of graphene. Applied Physics Reviews, 2021, 8, .	11.3	37
72	Electronic and optical properties of nonpolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>a</mml:mi></mml:math>-plane GaN quantum wells. Physical Review B, 2010, 82, .	3.2	36

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73	Towards predictive modeling of near-edge structures in electron energy-loss spectra of AlN-based ternary alloys. Physical Review B, 2011, 83, .	3.2	36
74	The significance of Bragg's law in electron diffraction and microscopy, and Bragg's second law. Acta Crystallographica Section A: Foundations and Advances, 2013, 69, 45-50.	0.3	36
75	Electrons seen in orbit. Nature, 1999, 401, 21-22.	27.8	35
76	The dissociation of the [aâ€‰+â€‰c] dislocation in GaN. Philosophical Magazine, 2013, 93, 3925-3938.	1.6	35
77	3D Strain in 2D Materials: To What Extent is Monolayer Graphene Graphite?. Physical Review Letters, 2019, 123, 135501.	7.8	35
78	Optical properties of GaN/AlGaN quantum wells grown on nonpolar substrates. Applied Physics Letters, 2008, 93, 101901.	3.3	34
79	Correlations between the morphology and emission properties of trench defects in InGaN/GaN quantum wells. Journal of Applied Physics, 2013, 113, .	2.5	34
80	The effect of dislocations on the efficiency of InGaN/GaN solar cells. Solar Energy Materials and Solar Cells, 2013, 117, 279-284.	6.2	34
81	Nanocathodoluminescence Reveals Mitigation of the Stark Shift in InGaN Quantum Wells by Si Doping. Nano Letters, 2015, 15, 7639-7643.	9.1	33
82	Characterization of InGaN quantum wells with gross fluctuations in width. Journal of Applied Physics, 2007, 102, .	2.5	31
83	Analysis of InGaN/GaN single quantum wells by X-ray scattering and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2003, 240, 297-300.	1.5	30
84	High excitation carrier density recombination dynamics of InGaN/GaN quantum well structures: Possible relevance to efficiency droop. Applied Physics Letters, 2013, 102, 022106.	3.3	29
85	Correlating electroluminescence characterization and physics-based models of InGaN/GaN LEDs: Pitfalls and open issues. AIP Advances, 2014, 4, .	1.3	29
86	Dislocations in AlGaN: Core Structure, Atom Segregation, and Optical Properties. Nano Letters, 2017, 17, 4846-4852.	9.1	29
87	Electronâ€beam induced crystallization transition in selfâ€developing amorphous AlF3 resists. Applied Physics Letters, 1996, 69, 170-172.	3.3	28
88	Degradation of InGaNâˆ•GaN laser diodes analyzed by microphotoluminescence and microelectroluminescence mappings. Applied Physics Letters, 2008, 92, 151110.	3.3	28
89	Temperature and Bias Dependent Trap Capture Cross Section in AlGaN/GaN HEMT on 6-in Silicon With Carbon-Doped Buffer. IEEE Transactions on Electron Devices, 2017, 64, 4868-4874.	3.0	28
90	The ABC model of recombination reinterpreted: Impact on understanding carrier transport and efficiency droop in InGaN/GaN light emitting diodes. Journal of Applied Physics, 2017, 122, 234505.	2.5	28

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91	Vertical leakage mechanism in GaN on Si high electron mobility transistor buffer layers. Journal of Applied Physics, 2018, 124, .	2.5	28
92	Imaging dislocation cores â€“ the way forward. Philosophical Magazine, 2006, 86, 4781-4796.	1.6	27
93	Coincident Electron Channeling and Cathodoluminescence Studies of Threading Dislocations in GaN. Microscopy and Microanalysis, 2014, 20, 55-60.	0.4	27
94	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. Journal of Applied Physics, 2018, 124, .	2.5	27
95	Insights into the origin of threading dislocations in GaNâˆ•Al2O3 from atomic force microscopy. Applied Physics Letters, 2006, 89, 011914.	3.3	26
96	Dielectric response of wurtzite gallium nitride in the terahertz frequency range. Solid State Communications, 2016, 247, 68-71.	1.9	26
97	Structural and Optical Emission Uniformity of m-Plane InGaN Single Quantum Wells in Coreâ€“Shell Nanorods. Crystal Growth and Design, 2016, 16, 1907-1916.	3.0	26
98	Structural properties of wurtzitelike ScGaN films grown by NH3-molecular beam epitaxy. Journal of Applied Physics, 2009, 106, 113533.	2.5	25
99	Direct Observation of Depth-Dependent Atomic Displacements Associated with Dislocations in Gallium Nitride. Physical Review Letters, 2014, 113, 135503.	7.8	25
100	Solution-Processed Epitaxial Growth of Arbitrary Surface Nanopatterns on Hybrid Perovskite Monocrystalline Thin Films. ACS Nano, 2020, 14, 11029-11039.	14.6	25
101	Optical polarization anisotropy of a-plane GaN/AlGaN multiple quantum well structures grown on r-plane sapphire substrates. Journal of Applied Physics, 2009, 105, 123112.	2.5	24
102	The atomic structure of polar and non-polar InGaN quantum wells and the green gap problem. Ultramicroscopy, 2017, 176, 93-98.	1.9	24
103	The effect of growth condition on the structure of 2H â€“ AlN films deposited on Si(111) by plasma-assisted molecular beam epitaxy. Journal of Materials Research, 1999, 14, 2036-2042.	2.6	23
104	Determination of relative internal quantum efficiency in InGaNâˆ•GaN quantum wells. Journal of Applied Physics, 2005, 98, 053509.	2.5	22
105	The effect of wafer curvature on x-ray rocking curves from gallium nitride films. Journal of Applied Physics, 2008, 103, .	2.5	22
106	The microstructure of non-polar a-plane (112Â¯0) InGaN quantum wells. Journal of Applied Physics, 2016, 119, .	2.5	22
107	Effects of KOH etching on the properties of Ga-polar n-GaN surfaces. Philosophical Magazine, 2006, 86, 2315-2327.	1.6	21
108	Low temperature photoluminescence and cathodoluminescence studies of nonpolar GaN grown using epitaxial lateral overgrowth. Journal of Applied Physics, 2010, 108, 033523.	2.5	21

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109	Structural impact on the nanoscale optical properties of InGaN core-shell nanorods. Applied Physics Letters, 2017, 110, .	3.3	21
110	High resolution transmission electron microscopy and three-dimensional atom probe microscopy as complementary techniques for the high spatial resolution analysis of GaN based quantum well systems. Materials Science and Technology, 2008, 24, 675-681.	1.6	20
111	The effects of Si-doped prelayers on the optical properties of InGaN/GaN single quantum well structures. Applied Physics Letters, 2014, 105, .	3.3	20
112	Effect of growth temperature and V/III-ratio on the surface morphology of MOVPE-grown cubic zincblende GaN. Journal of Applied Physics, 2018, 124, .	2.5	20
113	Mapping the potential within a nanoscale undoped GaAs region using a scanning electron microscope. Applied Physics Letters, 2004, 84, 2109-2111.	3.3	19
114	The origin and reduction of dislocations in Gallium Nitride. Journal of Materials Science: Materials in Electronics, 2008, 19, 208-214.	2.2	19
115	Assessment of the performance of scanning capacitance microscopy for n-type gallium nitride. Journal of Vacuum Science & Technology B, 2008, 26, 611-617.	1.3	19
116	Defect reduction in nonâ€polar (11$ ar 2 $0) GaN grown on (1$ ar 1 $02) sapphire. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1190-1193.	1.8	19
117	InGaN/GaN LEDs grown on Si(111): dependence of device performance on threading dislocation density and emission wavelength. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2168-2170.	0.8	19
118	Optimizing GaN () heteroâ€epitaxial templates grown on () sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 61-66.	1.5	19
119	Atomic Arrangement of a Z-Shape Faulted Dipole within Deformed GaAs. Physical Review Letters, 1998, 81, 5350-5353.	7.8	18
120	Growth of non-polar (11-20) InGaN quantum dots by metal organic vapour phase epitaxy using a two temperature method. APL Materials, 2014, 2, .	5.1	18
121	Enhancement mode operation in AlInN/GaN (MIS)HEMTs on Si substrates using a fluorine implant. Semiconductor Science and Technology, 2015, 30, 105007.	2.0	18
122	Comparative studies of efficiency droop in polar and non-polar InGaN quantum wells. Applied Physics Letters, 2016, 108, .	3.3	18
123	InGaN as a Substrate for AC Photoelectrochemical Imaging. Sensors, 2019, 19, 4386.	3.8	18
124	Exciton localization in InGaN/GaN single quantum well structures. Physica Status Solidi (B): Basic Research, 2003, 240, 344-347.	1.5	17
125	Highly conductive modulation doped composition graded p-AlGaN/(AlN)/GaN multiheterostructures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2009, 106, .	2.5	17
126	Low temperature carrier redistribution dynamics in InGaN/GaN quantum wells. Journal of Applied Physics, 2014, 115, .	2.5	17

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127	Dislocation-related trap levels in nitride-based light emitting diodes. Applied Physics Letters, 2014, 104, .	3.3	17
128	Control of threshold voltage in E-mode and D-mode GaN-on-Si metal-insulator-semiconductor heterostructure field effect transistors by in-situ fluorine doping of atomic layer deposition Al2O3 gate dielectrics. Applied Physics Letters, 2016, 108, .	3.3	17
129	Effect of humidity on the interlayer interaction of bilayer graphene. Physical Review B, 2019, 99, .	3.2	17
130	Electron energy loss spectroscopy studies of the amorphous to crystalline transition in FeF3. Journal of Applied Physics, 1999, 86, 2499-2504.	2.5	16
131	Resonant excitation photoluminescence studies of InGaNâ•GaN single quantum well structures. Applied Physics Letters, 2006, 89, 211901.	3.3	16
132	Practical issues in carrier-contrast imaging of GaN structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2576-2580.	0.8	16
133	Scanning capacitance microscopy studies of unintentional doping in epitaxial lateral overgrowth GaN. Journal of Applied Physics, 2009, 106, .	2.5	16
134	Low dislocation density nonpolar (11â€20) GaN films achieved using scandium nitride interlayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1778-1780.	0.8	16
135	Study of efficiency droop and carrier localisation in an InGaN/GaN quantum well structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2194-2196.	0.8	16
136	A study of the inclusion of prelayers in InGaN/GaN singleâ€•and multipleâ€quantumâ€•well structures. Physica Status Solidi (B): Basic Research, 2015, 252, 866-872.	1.5	16
137	Dislocation core structures in (0001) InGaN. Journal of Applied Physics, 2016, 119, .	2.5	16
138	Investigation of indium gallium nitride facet-dependent nonpolar growth rates and composition for coreâ€“shell light-emitting diodes. Journal of Nanophotonics, 2016, 10, 016010.	1.0	16
139	All-GaN-Integrated Cascode Heterojunction Field Effect Transistors. IEEE Transactions on Power Electronics, 2017, 32, 8743-8750.	7.9	16
140	Photoluminescence studies of cubic GaN epilayers. Physica Status Solidi (B): Basic Research, 2017, 254, 1600733.	1.5	16
141	Optical and microstructural properties of semi-polar (11-22) InGaN/GaN quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S727-S730.	0.8	15
142	Determination of the composition and thickness of semi-polar and non-polar III-nitride films and quantum wells using X-ray scattering. Journal of Applied Physics, 2012, 111, .	2.5	15
143	Growth, microstructure and morphology of epitaxial ScGaN films. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 33-40.	1.8	15
144	Properties of trench defects in InGaN/GaN quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 195-198.	1.8	15

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145	Dislocation core structures in Si-doped GaN. Applied Physics Letters, 2015, 107, .	3.3	15
146	Investigation of unintentional indium incorporation into GaN barriers of InGaN/GaN quantum well structures. Physica Status Solidi (B): Basic Research, 2015, 252, 928-935.	1.5	15
147	Growth and coalescence studies of oriented GaN on preâ€structured sapphire substrates using marker layers. Physica Status Solidi (B): Basic Research, 2016, 253, 46-53.	1.5	15
148	Comparative study of sputtered and spin-coatable aluminum oxide electron beam resists. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2737.	1.6	14
149	Electrically driven single InGaN/GaN quantum dot emission. Applied Physics Letters, 2008, 93, .	3.3	14
150	Carrier Density Dependent Localization and Consequences for Efficiency Droop in InGaN/GaN Quantum Well Structures. Japanese Journal of Applied Physics, 2013, 52, 08JK10.	1.5	14
151	Optical studies of nonâ€polar mâ€plane () InGaN/GaN multiâ€quantum wells grown on freestanding bulk GaN. Physica Status Solidi (B): Basic Research, 2015, 252, 965-970.	1.5	14
152	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. Journal of Applied Physics, 2016, 120, .	2.5	14
153	Solid-State Lighting Based on Light Emitting Diode Technology. , 2016, , 87-118.		14
154	Microtwin nucleation and propagation in heteroepitaxial II-VI compounds on (001)-oriented GaAs substrates. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1995, 72, 39-57.	0.6	13
155	Mechanisms of bending of threading dislocations in MOVPE-grown GaN on (0001) sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1750-1753.	0.8	13
156	Morphological study of non-polar (11-20) GaN grown on r-plane (1-102) sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1786-1788.	0.8	13
157	Atom probe tomography characterisation of a laser diode structure grown by molecular beam epitaxy. Journal of Applied Physics, 2012, 111, 053508.	2.5	13
158	Composition and luminescence studies of InGaN epilayers grown at different hydrogen flow rates. Semiconductor Science and Technology, 2013, 28, 065011.	2.0	13
159	A comparison of the optical properties of InGaN/GaN multiple quantum well structures grown with and without Si-doped InGaN prelayers. Journal of Applied Physics, 2016, 119, .	2.5	13
160	Mechanisms preventing trench defect formation in InGaN/GaN quantum well structures using hydrogen during GaN barrier growth. Physica Status Solidi (B): Basic Research, 2017, 254, 1600666.	1.5	13
161	Recombination from polar InGaN/GaN quantum well structures at high excitation carrier densities. Physical Review B, 2018, 98, .	3.2	13
162	TEM and PL characterisation of MBE-grown epitaxial GaN/GaAs. Materials Research Society Symposia Proceedings, 1996, 423, 311.	0.1	12

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163	High quantum efficiency InGaN/GaN structures emitting at 540 nm. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1970-1973.	0.8	12
164	High photoluminescence quantum efficiency InGaN multiple quantum well structures emitting at 380nm. Journal of Applied Physics, 2007, 101, 033516.	2.5	12
165	Very low dislocation density, resistive GaN films obtained using transition metal nitride interlayers. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1064-1066.	1.8	12
166	Atom probe reveals the structure of In_xGa_{1â€“x}N based quantum wells in three dimensions. Physica Status Solidi (B): Basic Research, 2008, 245, 861-867.	1.5	12
167	Coherent terahertz acoustic vibrations in polar and semipolar gallium nitride-based superlattices. Applied Physics Letters, 2009, 94, 011909.	3.3	12
168	A transmission electron microscopy study of microstructure evolution with increasing anneal temperature in Ti/Al ohmic contacts to n-GaN. Journal of Electronic Materials, 2001, 30, L13-L16.	2.2	11
169	A comparative study of near-UV emitting InGaN quantum wells with AlGaN and AlInGaN barriers. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1819-1823.	1.8	11
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